

Abstract Submitted
for the MAR08 Meeting of
The American Physical Society

Characterization of Epitaxial Graphene Oxide FAN MING, MICHAEL SPRINKLE, XUEBIN LI, XIAOSONG WU, Georgia Institute of Technology, CLAIRE BERGER, Georgia Institute of Technology - USA; CNRS - Institut Neel, Grenoble - France, WALTER DE HEER, Georgia Institute of Technology — Graphite oxide is a layered semiconducting material that is produced from graphite or graphene by chemical oxidation. The material is characterized by various probes such as transport, Raman spectroscopy and optical absorption spectroscopy. Here we present the properties of graphene oxide, which is chemically converted from epitaxial graphene directly on silicon carbide chips. The absorption spectrum indicates a large band gap and the Raman spectrum shows a pronounced D line while the 2D line is absent.

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Date submitted: 27 Nov 2007

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